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DEI1026

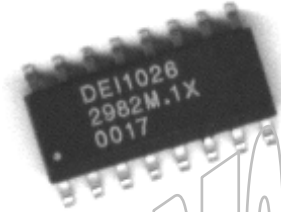
Six Channel

Discrete-to-Digital Interface

Sensing Open/Ground Signals

Features:

- Senses six Open/Ground Inputs
- Inputs are lightning protected to DO-160D Level 3
- TTL/CMOS-Compatible Tri-State Outputs
- Package / Temperature Options:
 - 16 lead .150" SOIC, -55°C /+85°C
 - 16 lead Ceramic 300mil SOP, -55°C /+125°C



SOIC package option shown

Functional Description:

The DEI1026 is a six channel discrete-to-digital interface BiCMOS device. It senses six Open/Ground discrete signals of the type commonly found in avionic systems. The inverted 3-state outputs are TTL/CMOS compatible and are enabled by the OE and CE pins. The inputs are lightning protected to meet the requirements of DO160D Sec 22 Waveforms 3, 4, and 5, Level 3. See figures 5-7. The device is available in a 16 lead .150 SOIC and .300 Ceramic SOP.

With its reliability, low cost, operating range, and lightning protection, the DEI1026 meets a large variety of interface requirements for aerospace applications.

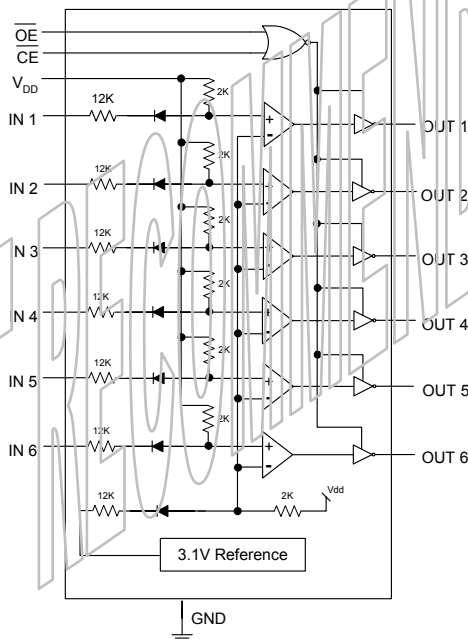


Figure 1: Function Diagram

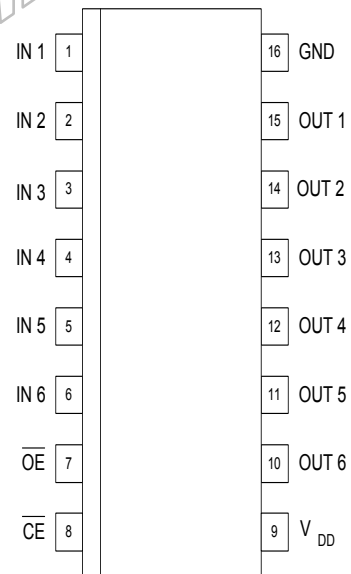


Figure 2: Pinout Diagram

Table 1: Absolute Maximum Ratings				
PARAMETER	MIN	MAX	UNITS	
Supply Voltage V_{DD}	-0.3	7.0	V	
Discrete Input Voltage (Pins 1-6)	-5	+40 *	V	
Digital Input Voltage (\overline{CE} and \overline{OE})	$V_{SS} - 0.3$	$V_{DD} + 0.3$	V	
Lightning Protection (Pins 1-6) DO160D, Waveform 3; Level 3 DO160D, Waveforms 4, and 5; Level 3	-600 -300	+600 +300	V	
Junction Temperature		145	°C	
Storage Temperature	Plastic Ceramic	-55 -55	150 150	°C
Operating Free Air Temperature	Plastic Ceramic	-55 -55	85 125	°C
The DEI1026 contains circuitry to protect inputs from damage due to electrostatic discharge. It has been characterized per JEDEC A114-A Human Body Model to Class 1. Observe precautions for handling and storing Electrostatic Sensitive Devices.				
* The DEI1026 will withstand the transient surge DC voltage step function loci limits for category B equipment per MIL-STD-704A.				

Table 2: DEI1026 Device Operating Characteristics						
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Supply Voltage	V_{DD}		4.5	5.0	5.5	V
Free Air Operating Temp.	T_A	$V_{DD} = 4.5 - 5.5$ V Plastic Ceramic	-55 -55		85 125	°C
Logic Output Sink Current	I_{OL}	$V_{DD} = 4.5 - 5.5$ V			5.0	mA
Logic Output Source Current	I_{OH}	$V_{DD} = 4.5 - 5.5$ V	-5.0			mA

Table 3: DEI1026 Logic Truth Table			
CE (Chip Enable)	OE (Output Enable)	Discrete Input	Output
0	0	Open	0
0	0	Ground	1
1	X	X	High Z
X	1	X	High Z

Table 4A: DEI1026-SES (Plastic) Electrical Characteristics
 (T_A = -55°C to +85°C, V_{DD} = 4.5 to 5.5 V, Unless otherwise noted)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Power Supply Characteristics						
Supply Current	I _{DD}	V _{IN} = V _{DD} (all inputs) V _{DD} = 5.5 V		5	10	mA
Discrete Input Characteristics						
Ground state input voltage	V _{SG}	Voltage source from input terminal to ground for Logic High Output.			3.0	V
Open state input voltage	V _{SO}	Voltage source from input terminal to ground for Logic Low Output.	3.5			V
Ground state input resistor	R _{IG}	Resistor from input to ground to guarantee Logic High Output.	0		100	Ω
Open state input resistor	R _{IO}	Resistor from input to ground to guarantee Logic Low Output.	100k			Ω
Input source current	I _{IO}	Current sourced into 100 Ohm resistor to Ground.	-100	-330		μA
Reverse leakage current	I _{IR}	V _{IN} = 35 V, V _{DD} = 0 V			100	μA
Logic Input Characteristics						
\overline{CE} , \overline{OE} input logic 1 level	V _{IH}		2.0			V
\overline{CE} , \overline{OE} input logic 0 level	V _{IL}				0.8	V
DC Output Characteristics						
Output logic 1 level (TTL)	V _{OH}	I _{OH} = -5 mA	2.4			V
Output logic 0 level (TTL)	V _{OL}	I _{OL} = 5 mA (2)			0.4	V
Output logic 1 level (CMOS)	V _{OH}	I _{OH} = -100 μA	V _{DD} - 50mV			V
Output logic 0 level (CMOS)	V _{OL}	I _{OL} = 100 μA			V _{SS} + 50mV	V
Off-state Output Current	I _{OZ}	$\overline{OE} = V_{DD}$ V _{DD} = 5.5 V V _{OUT} = 0 or V _{DD}			+/-10	μA
Switching Characteristics [1]						
I/O propagation delay	t _{HL} , t _{LH}	Refer to Figure 4.			150	ns
Delay from \overline{CE} or \overline{OE} input (with output low) to output HI-Z	t _{LZ}	Refer to Figure 3.			25	ns
Delay from \overline{CE} or \overline{OE} input (with output HI-Z) to output low	t _{ZL}	Refer to Figure 3.			25	ns
Delay from \overline{CE} or \overline{OE} input (with output high) to output HI -Z	t _{HZ}	Refer to Figure 3.			25	ns
Delay from \overline{CE} or \overline{OE} input (with output HI-Z) to output high	t _{ZH}	Refer to Figure 3.			25	ns

Table 4B: DEI1026-WM[] (Ceramic) Electrical Characteristics
 (T_A = -55°C to +125°C, V_{DD} = 4.5 to 5.5 V, Unless otherwise noted)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Power Supply Characteristics						
Supply Current	I _{DD}	V _{IN} = V _{DD} (all inputs) V _{DD} = 5.5 V		5	10	mA
Discrete Input Characteristics						
Ground state input voltage	V _{SG}	Voltage source from input terminal to ground for Logic High Output.			3.0	V
Open state input voltage	V _{SO}	Voltage source from input terminal to ground for Logic Low Output.	3.5			V
Ground state input resistor	R _{IG}	Resistor from input to ground to guarantee Logic High Output.	0		100	Ω
Open state input resistor	R _{IO}	Resistor from input to ground to guarantee Logic Low Output.	100k			Ω
Input source current	I _{IO}	Current sourced into 100 Ohm resistor to Ground.	-100	-330		μA
Reverse leakage current	I _{IR}	V _{IN} = 35 V, V _{DD} = 0 V			100	μA
Logic Input Characteristics						
\overline{CE} , \overline{OE} input logic 1 level	V _{IH}		2.0			V
\overline{CE} , \overline{OE} input logic 0 level	V _{IL}				0.8	V
DC Output Characteristics						
Output logic 1 level (TTL)	V _{OH}	I _{OH} = -5 mA	2.4			V
Output logic 0 level (TTL)	V _{OL}	I _{OL} = 5 mA (2)			0.4	V
Output logic 1 level (CMOS)	V _{OH}	I _{OH} = -100 μA	V _{DD} - 50mV			V
Output logic 0 level (CMOS)	V _{OL}	I _{OL} = 100 μA			V _{SS} + 50mV	V
Off-state Output Current	I _{OZ}	$\overline{OE} = V_{DD}$ V _{DD} = 5.5 V V _{OUT} = 0 or V _{DD}			+/-10	μA
Switching Characteristics [1]						
I/O propagation delay	t _{HL} , t _{LH}	Refer to Figure 4.			170	ns
Delay from \overline{CE} or \overline{OE} input (with output low) to output HI-Z	t _{LZ}	Refer to Figure 3.			30	ns
Delay from \overline{CE} or \overline{OE} input (with output HI-Z) to output low	t _{ZL}	Refer to Figure 3.			30	ns
Delay from \overline{CE} or \overline{OE} input (with output high) to output HI -Z	t _{HZ}	Refer to Figure 3.			30	ns
Delay from \overline{CE} or \overline{OE} input (with output HI-Z) to output high	t _{ZH}	Refer to Figure 3.			30	ns

Notes:

1. Guaranteed by design and not production tested.
2. Limit the sum of all IOL currents to 20ma. The Vsg spec may exceed limit beyond this current.

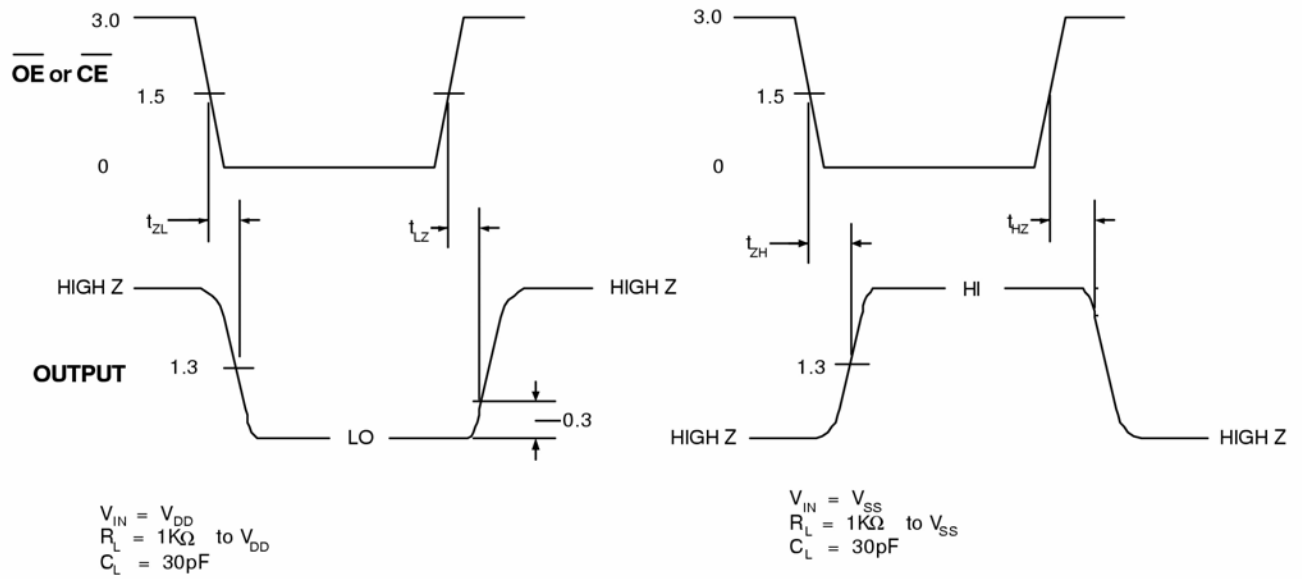


Figure 3: Enable to Output Propagation Delay

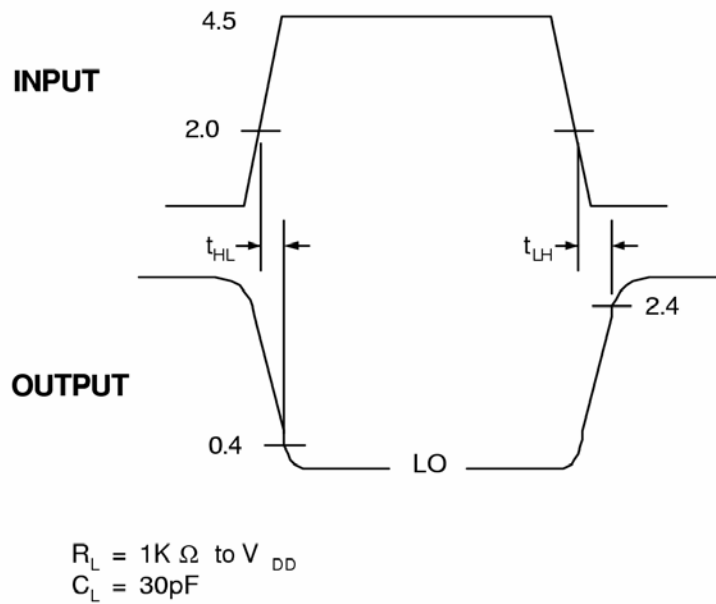


Figure 4: Input to Output Propagation Delay

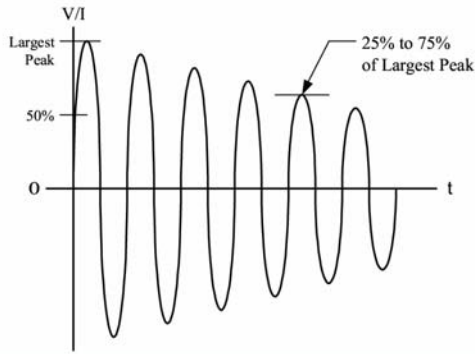


Figure 5: DO160D Voltage Waveform #3
 $V_{OC} = 600V$, $I_{SC} = 24A$, Frequency = 1.0MHZ $\pm 20\%$

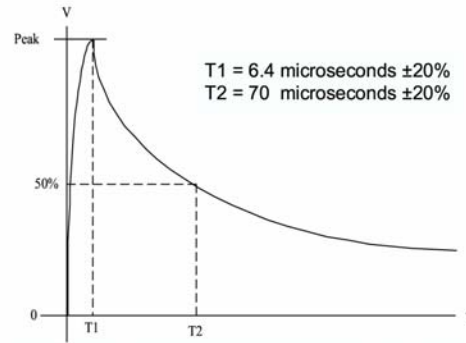


Figure 6: DO160D Voltage Waveform #4
 $V_{OC} = 300V$, $I_{SC} = 60A$

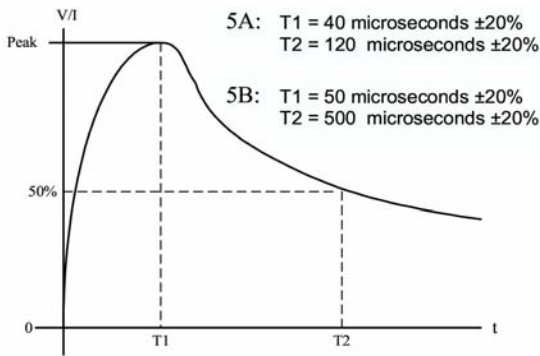


Figure 7: DO160D Voltage Waveform #5
 $V_{OC} = 300V$, $I_{SC} = 300A$

Notes:

1. V_{OC} = Peak Open Circuit Voltage available at the calibration point.
2. I_{SC} = Peak Short Circuit Current available at the calibration point.
3. Amplitude tolerances: +10%, -0%
4. The ratio of V_{OC} to I_{SC} is the generator source impedance to be used for generator calibration purposes.

Table 5: Package Characteristics

PACKAGE TYPE	16 Lead SOIC Narrow Body	16 Lead SOIC Narrow Body, Green	16 Lead Ceramic SOP
REFERENCE	16L SOIC NB	16L SOIC NB G	16L CSOP
THERMAL RESISTANCE:			
θ_{JA} (4 layer PCB with Power Planes)	74 °C/W	74 °C/W	-
θ_{JC}	24 °C/W	24 °C/W	23 °C/W
JEDEC MOISTURE SENSITIVITY LEVEL (MSL)	MSL 2 / 235°C	MSL 2 / 260°C	Hermetic
LEAD FINISH MATERIAL / JEDEC Pb-free CODE	SnPb	NiPdAu e4	Au e4
Pb-Free DESIGNATION	Not Pb-free	RoHS Compliant	Pb Free
JEDEC REFERENCE	MS-012-AC	MS-012-AC	-

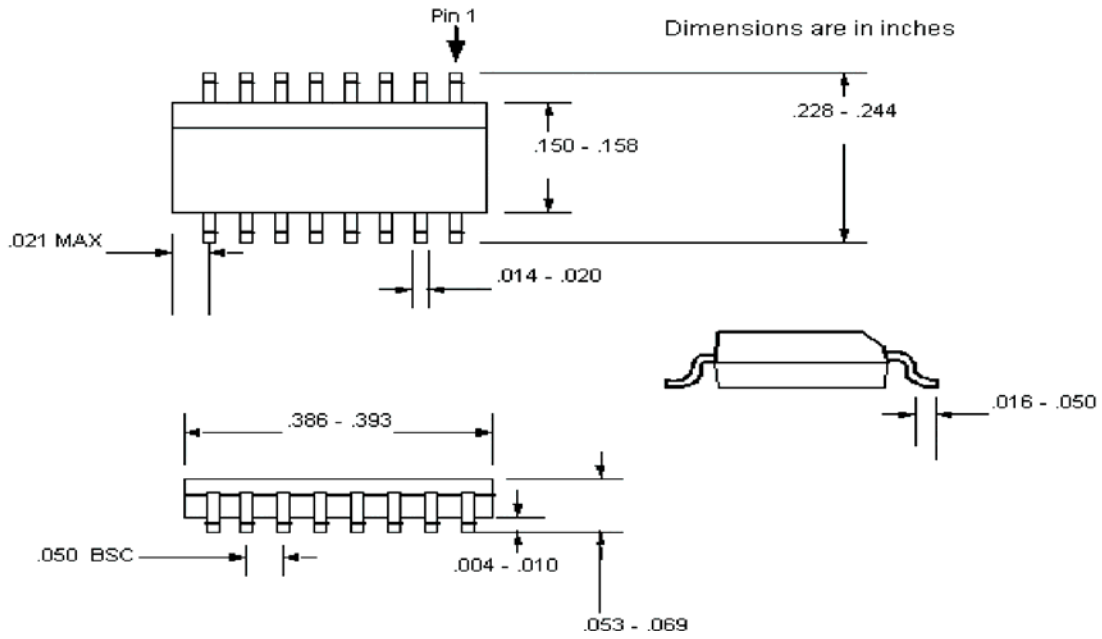


Figure 8: Mechanical Outline, 16 lead 0.150" SOIC

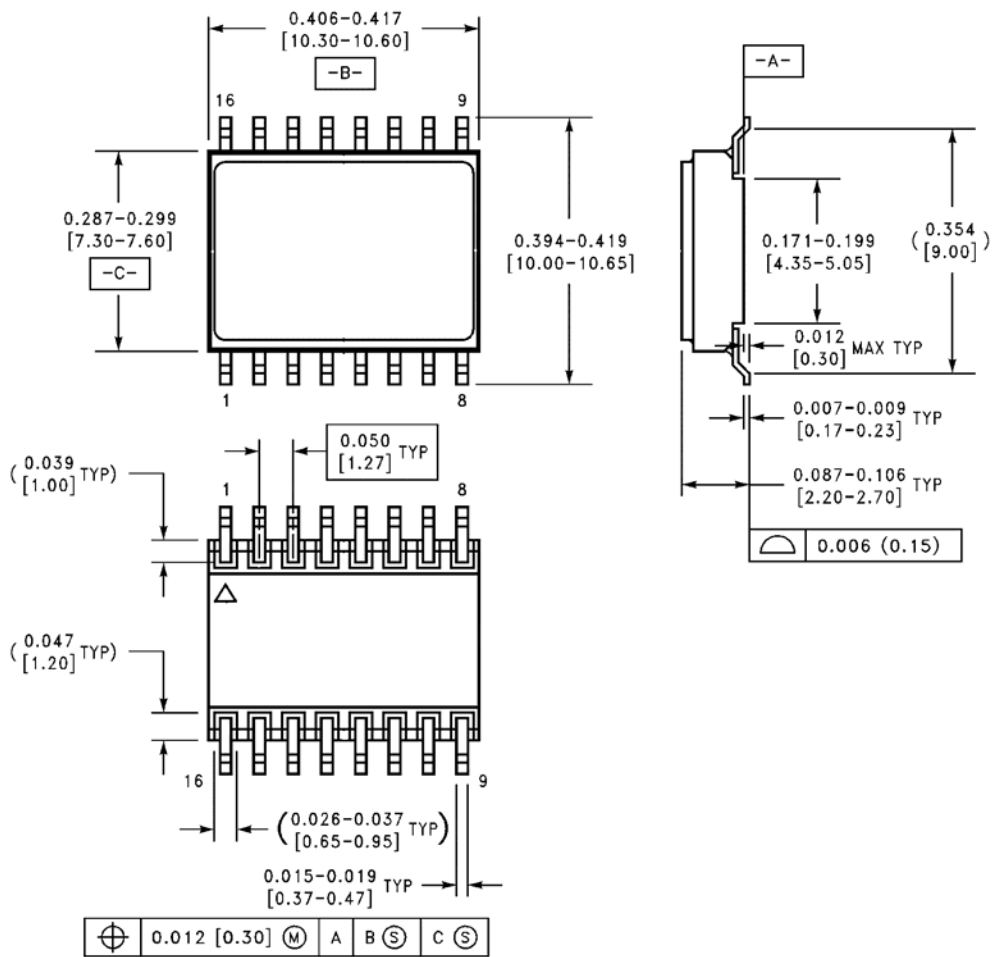


Figure 9: Mechanical Outline, 16 lead Ceramic SOP

Table 6: Ordering Information

DEI PART NUMBER	MARKING (1)	PACKAGE	OP. TEMP. RANGE	PROCESSING
DEI1026	DEI1026	16L SOIC NB	-55 / +85°C	Standard
DEI1026-G	DEI1026 E4 (2)	16L SOIC NB G	-55 / +85°C	Standard
DEI1026-WMS	DEI1026-WMS	16 lead ceramic SOP	-55 / +125°C	Standard
DEI1026-WMB	DEI1026-WMB	16 lead ceramic SOP	-55 / +125°C	Burn In, 96 hr @125°C

NOTES:
1. All packages marked with Lot Code and Date Code.
2. "E4" after Date Code Denotes Pb Free category.

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